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MURAXXT3G-MS

Product specification



SURFACE MOUNT ULTRAFAST POWER RECTIFIERS DIODES**VOLTAGE RANGE: 50 - 600V****CURRENT: 2.0A****Features**

- Glass Passivated Die Construction
- Ideally Suited for Automatic Assembly
- Low Forward Voltage Drop, High Efficiency
- Low Power Loss
- Super-Fast Recovery Time
- Plastic Case Material has UL Flammability Classification Rating 94V-0

Mechanical Data

- Case: SMA/DO-214AC, Molded Plastic
- Terminals: Solder Plated, Solderable
- per MIL-STD-750, Method 2026
- Polarity: Cathode Band or Cathode Notch
- Weight: 0.064 grams (approx.)

Reference News

PACKAGE OUTLINE	Marking
	
SMA(DO-214AC)	*** Representative VRRM

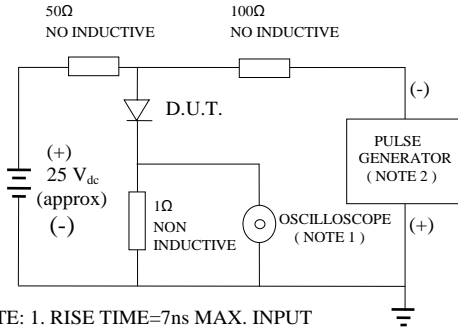
Maximum Ratings and Electrical Characteristics $T_A = 25^\circ\text{C}$ unless otherwise specified Single phase, half wave, 60Hz, resistive or inductive load. For capacitive load, derate current by 20%.

Characteristic	Symbol	MURA 205T3G- MS	MURA 210T3G- MS	MURA 215T3G- MS	MURA 220T3G- MS	MURA 230T3G- MS	MURA 240T3G- MS	MURA 260T3G- MS	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	50	100	150	200	300	400	600	V
RMS Reverse Voltage	$V_{R(RMS)}$	35	70	105	140	210	280	420	V
Average Rectified Output Current @ $T_L = 75^\circ\text{C}$	I_o	2.0							A
Non-Repetitive Peak Forward Surge Current 8.3ms Single half sine-wave superimposed on rated load (JEDEC Method)	I_{FSM}	40				35			A
Forward Voltage @ $I_F = 2.0\text{A}$	V_{FM}	0.95				1.25			V
Peak Reverse Current At Rated DC Blocking Voltage	@ $T_A = 25^\circ\text{C}$ @ $T_A = 120^\circ\text{C}$ I_{RM}	5.0 250							μA
Reverse Recovery Time (Note 1)	t_{rr}	35						nS	
Typical Junction Capacitance (Note 2)	C_j	20				50			pF
Typical Thermal Resistance (Note 3)	$R_{\theta JL}$	40						$^\circ\text{C/W}$	
Operating and Storage Temperature Range	T_j, T_{STG}	-65 to +150						$^\circ\text{C}$	

Note: 1.Reverse recovery condition $I_F=0.5\text{A}, I_R=1.0\text{A}, I_{rr}=0.25\text{A}$
 2.Measured at 1MHz and applied reverse voltage of 4.0V D.C.
 3.P.C.B. mounted with 0.2x0.2"(5.0x5.0mm) copper pad areas

RATINGS AND CHARACTERISTIC CURVE MURAXXT3G-MS

FIG. 1-TEST CIRCUIT DIAGRAM AND REVERSE RECOVERY TIME CHARACTERISTIC



NOTE: 1. RISE TIME=7ns MAX. INPUT IMPEDANCE=1 MOhms 22PF
2. RISE TIME =10ns MAX. SOURCE IMPEDANCE=50 OHMS

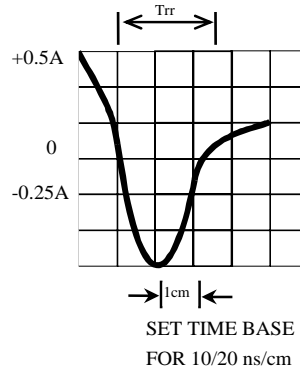


FIG. 2-TYPICAL FORWARD CURRENT DERATING CURVE

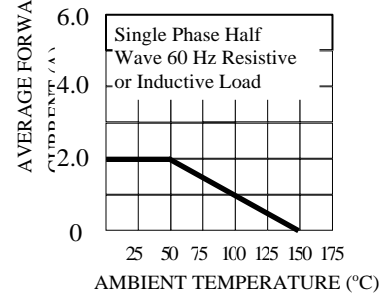


FIG. 3-TYPICAL REVERSE CHARACTERISTICS

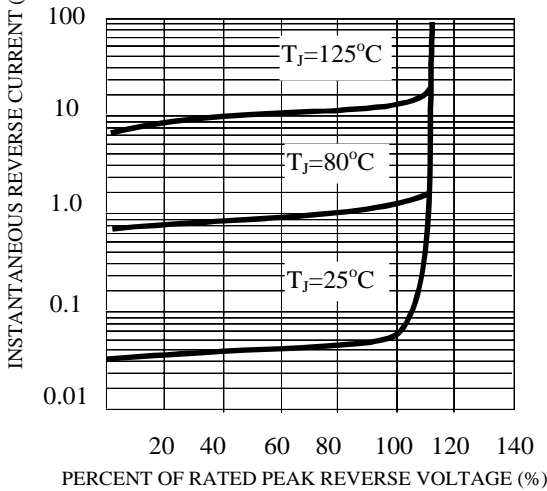


FIG. 4-TYPICAL INSTANTANEOUS FORWARD CHARACTERISTICS

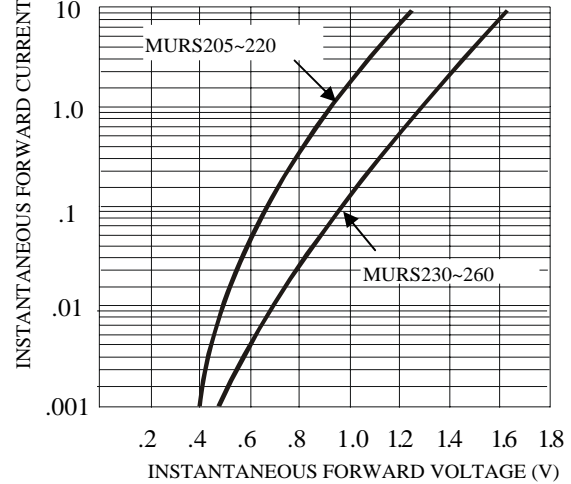


FIG. 5-MAXIMUM NON-REPETITIVE FORWARD SURGE CURRENT

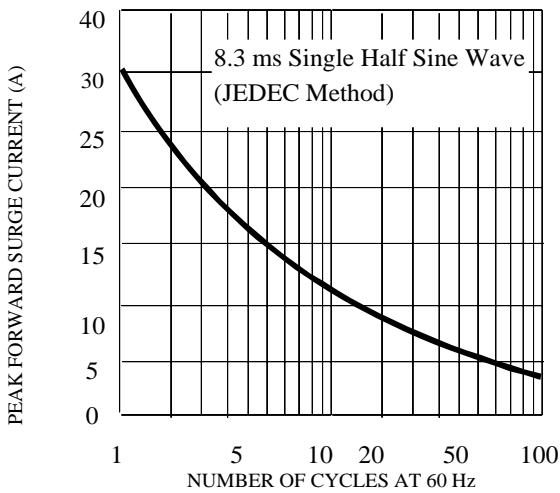
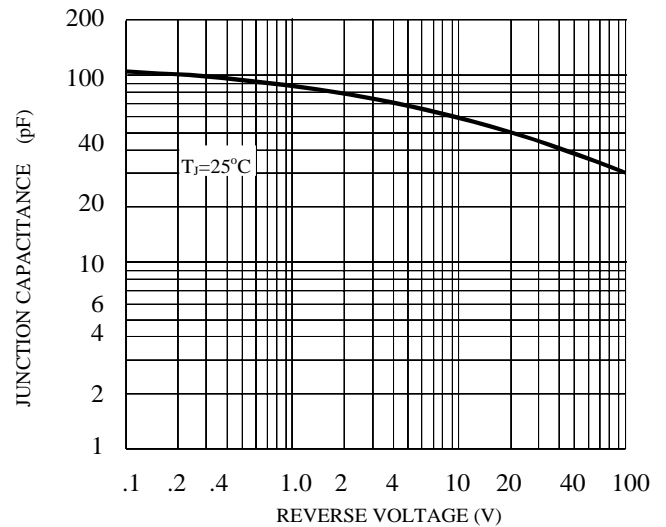
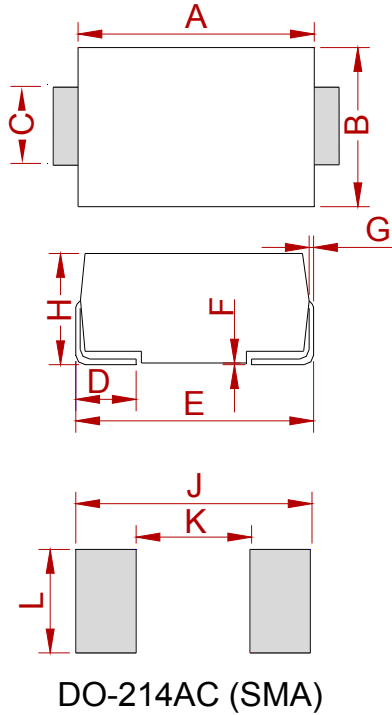


FIG. 6-TYPICAL JUNCTION CAPACITANCE



PACKAGE MECHANICAL DATA



Ref.	Dimensions			
	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	4.25	4.65	0.167	0.183
B	2.50	2.90	0.098	0.114
C	1.35	1.65	0.053	0.065
D	0.76	1.52	0.030	0.060
E	4.93	5.28	0.194	0.208
F	0.051	0.203	0.002	0.008
G	0.15	0.31	0.006	0.012
H	1.98	2.41	0.078	0.095
J	6.50		0.256	
K		2.30		0.090
L	1.70		0.067	

REEL SPECIFICATION

P/N	PKG	QTY
MURAXXT3G-MS	DO-214AC(SMA)	2000

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